A. FURTHER INFORMATION ABOUT OUR GROUP

1. Incorporation of Our Company

Our Company was established in the PRC on September 17, 2019 as a limited liability company and was converted to a joint stock company with limited liability under the laws of the PRC on June 25, 2025.

As of the date of this document, our Company's registered office is located at 1-608, 6 Lianhui Street, Xixing Subdistrict, Binjiang District Hangzhou, Zhejiang Province, PRC. Our Company has established a principal place of business in Hong Kong at 31 Tower Two, Times Square, 1 Matheson Street, Causeway Bay, Hong Kong and has been registered as a non-Hong Kong company under Part 16 of the Companies Ordinance on June 30, 2025. Mr. Wong Chun Wing Samuel, our company secretary, has been appointed as the authorized representative of our Company for the acceptance of service of process in Hong Kong, whose correspondence address is 31 Tower Two, Times Square, 1 Matheson Street, Causeway Bay, Hong Kong.

As our Company was established in the PRC, our corporate structure and Articles of Association are subject to the relevant laws and regulations of the PRC. A summary of the relevant provisions of our Articles of Association is set out in "Appendix VI — Summary of the Articles of Association." A summary of certain relevant aspects of the laws and regulations of the PRC is set out in "Appendix V — Summary of Principal Legal and Regulatory Provisions."

2. Changes in Share Capital of Our Company

As of the date of our establishment as a joint stock limited company, our registered capital was RMB50,000,000 divided into 50,000,000 Shares with a par value of RMB1.00 each. We also expect to conduct a [**REDACTED**] immediately prior to the [**REDACTED**], pursuant to which each Share in our issued share capital will be [**REDACTED**] into [**REDACTED**] Shares. Immediately after the [**REDACTED**] and before the [**REDACTED**], the registered share capital of our Company will be RMB50,000,000 with [**REDACTED**] Shares in a nominal value of RMB[**REDACTED**] each.

Upon completion of the [**REDACTED**] and the conversion of Unlisted Shares into H Shares, taking into account the [**REDACTED**] and assuming that the [**REDACTED**] is not exercised and no other changes are made to the issued share capital of our Company between the Latest Practicable Date and [**REDACTED**], our Company's registered capital will be increased to approximately RMB[**REDACTED**] comprising [**REDACTED**] Unlisted Shares of RMB[**REDACTED**] each and [**REDACTED**] H Shares of RMB[**REDACTED**] each, representing approximately [**REDACTED**]% and [**REDACTED**]% of our registered capital, respectively.

Save as disclosed in the section headed "History, Development and Corporate Structure" and above, there has been no alteration in the share capital of our Company within the two years immediately preceding the date of this document.

3. Shareholders' Resolutions

In accordance with the Shareholders' resolutions of our Company dated June 26, 2025, among other things, the following resolutions were passed by the Shareholders:

(a) the [**REDACTED**] of the Shares with nominal value of RMB1.0 each on the basis of [**REDACTED**], effective immediately prior to the [**REDACTED**], and taking into account the [**REDACTED**], the [**REDACTED**] by our Company of H Shares of nominal value of RMB[**REDACTED**] each and such H Shares be [**REDACTED**] on the Stock Exchange;

(b) the number of H Shares to be issued before the exercise of the [**REDACTED**] shall not exceed 20% of the enlarged share capital of our Company upon completion of the [**REDACTED**] and granting the [**REDACTED**] the [**REDACTED**] of no more than [**REDACTED**]% of the above number of H Shares to be issued;

(c) subject to CSRC's approval, upon completion of the [**REDACTED**], [**REDACTED**] Unlisted Shares held by certain existing Shareholders will be converted into H Shares;

(d) authorization of the Board and its authorized persons to handle all matters relating to, among other things, the [**REDACTED**], the [**REDACTED**] and [**REDACTED**] of the H Shares; and

(e) subject to the completion of the [**REDACTED**], the conditional adoption of the Articles of Association, which shall become effective on the [**REDACTED**], and the Board has been authorized to amend the Articles of Association in accordance with relevant laws and regulations and upon the request from the Stock Exchange and relevant PRC regulatory authorities.

4. Subsidiaries of our Company and changes in share capital of our subsidiaries

The list of our subsidiaries is set out in the Accountant's Report, the text of which is set out in Appendix I to this document.

Save as disclosed in the section headed "History, Development and Corporate Structure", no alteration in the share capital of our subsidiaries had taken place within the two immediately preceding the date of this document.

5. Restriction on Share Repurchase

Please refer to the section headed "Appendix V — Summary of Principal Legal and Regulatory Provisions — Share Buy-Back" in this document for details.

B. FURTHER INFORMATION ABOUT OUR BUSINESS

1. Summary of Material Contracts

The following contracts (not being contracts entered into in the ordinary course of business) have been entered into by us or any of our subsidiaries within the two years preceding the date of this document that are or may be material:

(a) the supplemental agreement dated June 24, 2025, entered into between (1) our Company, (2) Vasona Technology Hong Kong Limited, (3) Hangzhou Xidaxin Corporate Management Partnership (L.P.)* (杭州喜達芯企業管理合夥企業(有限合夥)), (4) Hangzhou Xihangxin Corporate Management Partnership (L.P.)* (杭州喜杭芯企業管理合夥企業(有限合夥)), (5) Hangzhou Moxin Corporate Management Partnership (L.P.)* (杭州模芯企業管理合夥企業(有限合夥)), (6) Smart Wealth Limited Partnership (智富有限合夥企業), (7) Smart Advantage Limited Partnership (智益有限合夥企業), (8) Hangzhou Haibang Qiyue Equity Investment Partnership (L.P.)* (杭州海邦啟悅股權投資合夥企業(有限合夥)), (9) Smart Brilliant International Investment Limited (智晶國際投資有限公司), (10) Zhuhai Weiheng Equity Investment Partnership (L.P.)* (珠海巍恒股權投資合夥企業(有限合夥)), (11) HSG Growth VI Holdco B (HK) Limited (previously known as SCC GROWTH VI HOLDCO B (HK) LIMITED), (12) Beijing Junlian Shengyuan Equity Investment Partnership (L.P.)* (北京君聯晟源股權投資合夥企業(有限合夥)), (13) Zhuhai Junlian Xingze Equity Investment Enterprise (L.P.)* (珠海君聯星澤股權投資企業(有限合夥)), (14) Hai Feng Investment Holding Limited (海風投資有限公司), (15) Hangzhou Xinshengwei Equity Investment Partnership L.P.)* (杭州芯盛微股權投資合夥企業(有限合夥)), (16) Hefei Huaxin Kerui IC Investment Partnership (L.P.)* (合肥華芯科瑞集成電路投資合夥企業(有限合夥)), (17) Hefei Huadeng Erqi IC Industry Investment Partnership (L.P.)* (合肥華登二期集成電路產業投資合夥企業(有限合夥)), (18) Cosmic Warrior (HK) Limited, (19) Hubei Xiaomi Changjiang Industry Fund Partnership (L.P.)* (湖北小米長江產業基金合夥企業(有限合夥)), (20) Contemporary Amperex Technology Co., Limited (寧德時代新能源科技股份有限公司), (21) Huh Youm, (22) National IC Industry Investment Fund Phase II Co., Ltd.* (國家集成電路產業投資基金二期股份有限公司), (23) Hangzhou Xinchengwei

Equity Investment Partnership L.P.)* (杭州芯成微股權投資合夥企業(有限合夥), (24) Hangzhou Xinyuwei Equity Investment Partnership (L.P.)* (杭州芯宇微股權投資合夥企業(有限合夥)), (25) Guangzhou Guangqi Xinmai Management Consultancy Partnership (L.P.)* (廣州廣祺欣邁管理諮詢合夥企業(有限合夥)), (26) Zhuhai Hongtu Zhanlu Equity Investment Partnership (L.P.)* (珠海市紅土湛盧股權投資合夥企業(有限合夥)), (27) Jiaxing Hengjunbang Equity Investment Partnership (L.P.)* (嘉興恒雋邦股權投資合夥企業(有限合夥)), (28) Hangzhou Fuyang Xiangheng Equity Investment Partnership (L.P.)* (杭州富陽項恒股權投資合夥企業(有限合夥)), (29) Suzhou Huaye Zhiyuan No. 3 Equity Investment Partnership (L.P.)* (蘇州華業致遠三號股權投資合夥企業(有限合夥)), (30) Jiaxing Taixin Keqi Venture Investment Partnership (L.P.)* (嘉興泰芯科啟創業投資合夥企業(有限合夥)), (31) Hangzhou Xingcheng Lianxin Venture Investment Partnership (L.P.)* (杭州星成聯芯創業投資合夥企業(有限合夥)), (32) Hangzhou Yuxin Venture Investment Partnership (L.P.)* (杭州寓鑫創業投資合夥企業(有限合夥)), (33) Yibin Lvneng Equity Investment Partnership (L.P.)* (宜賓綠能股權投資合夥企業(有限合夥)), (34) Guangdong Changtuoshi Venture Investment Partnership (L.P.)* (廣東長拓石創業投資合夥企業(有限合夥)), (35) Hangzhou Xinlanwei Venture Investment Partnership (L.P.)* (杭州芯嵐微創業投資合夥企業(有限合夥)), (36) Zhuhai Junlian Xingchi Venture Investment Enterprise (L.P.)* (珠海君聯星馳創業投資企業(有限合夥)), (37) Hangzhou Huaxin Yunmai Equity Investment Partnership (L.P.)* (杭州華芯雲邁股權投資合夥企業(有限合夥)), (38) Yibin Chendao New Energy Industry Equity Investment Partnership (L.P.)* (宜賓晨道新能源產業股權投資合夥企業(有限合夥)), (39) Zhejiang Jinkong Investment Co., Ltd.* (浙江金控投資有限公司) (currently known as Zhejiang Province Innovation Capital Investment Co., Ltd.* (浙江省創新資本投資有限公司), (40) Hangzhou Haibang Ruibo Equity Investment Partnership (L.P.)* (杭州海邦睿柏股權投資合夥企業(有限合夥)), (41) Ningbo Haibang Xingcai Venture Investment Partnership (L.P.)* (寧波海邦星材創業投資合夥企業(有限合夥)), and (42) Qingdao Jingque Xinyang Technology Center (L.P.)* (青島精確芯陽科技中心(有限合夥)), in relation to the termination of special rights; and

(b) the [**REDACTED**].

2. Our Intellectual Property Rights

(a) Trademarks

As of the Latest Practicable Date, we had registered the following trademarks which we consider to be or may be material to our business:

No.	Trademark	Registered Owner	Registration No.	Class	Expiry Date	Place of Registration
1.	芯迈半导体	our Company	60797136	42	May 13, 2032	PRC
2.	芯迈	our Company	60774956	42	May 13, 2032	PRC
3.		our Company	65306186	42	November 27, 2032	PRC
4.		our Company	65310406	9	November 27, 2032	PRC
5.		our Company	65322753	9	November 27, 2032	PRC
6.		our Company	65305779	42	November 27, 2032	PRC
7.	芯迈	our Company	64924102	9	March 27, 2033	PRC
8.	芯迈半导体	our Company	60770749	9	April 6, 2033	PRC
9.	芯迈半导体	our Company	67210495	9	June 13, 2033	PRC
10.		our Company	68938697	40	July 6, 2033	PRC

No.	Trademark	Registered Owner	Registration No.	Class	Expiry Date	Place of Registration
11.		our Company	68941046	40	July 6, 2033	PRC
12.	芯迈半导体	our Company	68936312	40	July 20, 2033	PRC
13.	芯迈	our Company	68941029	40	July 6, 2033	PRC
14.	SILICON MAGIC	our Company	72569224	9	December 13, 2034	PRC
15.	MAGICFAST	our Company	77185704	9	August 20, 2034	PRC
16.	HPD PACK	our Company	81287459	9	April 19, 2035	PRC
17.	Silicon Magic	our Company	305895659	9, 42	March 2, 2032	Hong Kong
18.	A 芯迈 B 芯邁	our Company	305895631	9, 42	March 2, 2032	Hong Kong
19.	A 芯迈半导体 B 芯邁半導體	our Company	305895640	9, 42	March 2, 2032	Hong Kong
20.		our Company	306901605	9, 42	March 15, 2035	Hong Kong
21.		our Company	306901614	9, 42	March 15, 2035	Hong Kong
22.	芯邁半導體	our Company	02237384	42	July 15, 2032	Taiwan
23.	芯邁半導體	our Company	02235288	9	July 15, 2032	Taiwan
24.	芯迈	our Company	02237383	42	July 15, 2032	Taiwan
25.	芯迈	our Company	02235287	9	July 15, 2032	Taiwan
26.	Silicon Magic	our Company	02237382	42	July 15, 2032	Taiwan
27.	Silicon Magic	our Company	02235286	9	July 15, 2032	Taiwan
28.	Silicon Magic	our Company	40-2123534	9, 42	December 5, 2033	South Korea
29.	SILICON MAGIC	our Company	7,930,964	9, 42	September 1, 2035	United States
30.	SILICON TOP	Hangzhou Xintong	79256579	9	December 6, 2034	PRC
31.		Hangzhou Xintong	77168771	9	August 27, 2034	PRC
32.		Hangzhou Xintong	77171241	42	August 27, 2034	PRC
33.	SMARTPACK	Hangzhou Xintong	73800779	40	February 20, 2034	PRC
34.	芯通	Hangzhou Xintong	73818269	9	April 27, 2034	PRC
35.	芯通半导体	Hangzhou Xintong	73816135	40	April 27, 2034	PRC
36.	芯通	Hangzhou Xintong	73808147	40	April 27, 2034	PRC
37.	芯通半导体	Hangzhou Xintong	73815736	9	April 27, 2034	PRC
38.	Silicon Mitus	SMI	23819459	9	April 13, 2028	PRC
39.	Silicon Mitus	SMI	23819458	42	April 13, 2028	PRC
40.	Silicon Mitus	SMI	5568169	9	September 24, 2028	United States

No.	Trademark	Registered Owner	Registration No.	Class	Expiry Date	Place of Registration
41.	Silicon Mitus	SMI	5568170	42	September 24, 2028	United States
42.	Silicon Mitus	SMI	40-1295825	9	October 19, 2027	South Korea
43.	Silicon Mitus	SMI	40-1267850	42	July 9, 2027	South Korea
44.	실리콘마이터스	SMI	40-1295824	9	October 19, 2027	South Korea
45.	실리콘마이터스	SMI	40-1267849	42	July 9, 2027	South Korea
46.	Silicon Mitus	SMI	40-1295826	9	October 19, 2027	South Korea
47.	Silicon Mitus	SMI	40-1267851	42	July 9, 2027	South Korea
48	Silicon Magic	our Company	019267648	9, 42	October 28, 2035	European Union

As of the Latest Practicable Date, we had applied for the following trademarks which we consider to be or may be material to our business:

No.	Trademark	Registered Owner	Application No.	Class	Application Date	Place of Registration
1.	Silicon Magic	our Company	7300979	9	October 22, 2025	India
2.	Silicon Magic	our Company	7300980	42	October 22, 2025	India
3	Thermal Well	our Company	90441304	9, 42	March 9, 2026	PRC

(b) Patents

As of the Latest Practicable Date, we are the registered owner of or had the right to use the following patents which we consider to be or may be material to our business:

No.	Patent	Patentee	Patent Number	Patent Type	Expiry Date	Place of Registration
1.	Shielded-gate-trench semiconductor structure and shielded-gate-trench semiconductor device (屏蔽柵極溝槽半導體結構與屏蔽柵極溝槽半導體器件)	our Company	CN202111170323.1	Invention Patent	October 7, 2041	PRC
2.	Super-junction power device and manufacturing method thereof (一種超結功率器件及其製造方法)	our Company	CN202411247783.3	Invention Patent	September 5, 2044	PRC
3.	Overcurrent protection circuit used with charge pump and the control method thereof (一種電荷泵的過電流保護電路及其控制方法)	our Company	CN202410554568.1	Invention Patent	May 6, 2044	PRC
4.	Trench-type MOSFET and method for manufacturing the same (一種溝槽型MOSFET及製造方法)	our Company	CN202310979907.6	Invention Patent	August 3, 2043	PRC

No.	Patent	Patentee	Patent Number	Patent Type	Expiry Date	Place of Registration
5. . .	Power semiconductor device (一種功率半導體器件)	our Company	CN202411146981.0	Invention Patent	August 19, 2044	PRC
6. . .	Bias circuit and the bias voltage control method thereof (一種偏置電路及其偏置電壓控制方法)	our Company	CN202410469084.7	Invention Patent	April 17, 2044	PRC
7. . .	Cellular structure and layout of silicon carbide trench gate MOSFET (一種碳化矽溝槽柵MOSFET的元胞結構及版圖)	our Company	CN202410381072.9	Invention Patent	March 28, 2044	PRC
8. . .	Split-gate MOSFET and manufacturing method thereof (分離柵MOSFET及其製造方法)	our Company	CN202111635852.4	Invention Patent	December 28, 2041	PRC
9. . .	Trench-type semiconductor power device and layout (一種溝槽型半導體功率器件及版圖)	our Company	CN202311468016.0	Invention Patent	November 5, 2043	PRC
10. .	Trench-type power device and manufacturing method thereof (一種溝槽型功率器件及其製備方法)	our Company	CN202311586903.8	Invention Patent	November 23, 2043	PRC
11. .	Super-junction device and manufacturing method thereof (超結器件及其製造方法)	our Company	CN202111098970.6	Invention Patent	September 17, 2041	PRC
12. .	Gate-source structure and manufacturing method thereof, and asymmetric trench MOSFET and manufacturing method thereof (柵源結構及製造方法、非對稱溝槽型MOSFET及製造方法)	our Company	CN202310428937.8	Invention Patent	April 17, 2043	PRC
13. .	Trench-type semiconductor power device and layout (一種溝槽型半導體功率器件及版圖)	our Company	CN202310582449.2	Invention Patent	May 18, 2043	PRC
14. .	Method for manufacturing conducting path in doped region, trench-type MOSFET device and manufacturing method thereof (用於摻雜區的導電通道的製造方法、溝槽型MOSFET器件及其製造方法)	our Company	CN202111078843.X	Invention Patent	September 14, 2041	PRC
15. .	Contact structure of semiconductor device and manufacturing method thereof (一種半導體器件的接觸結構及其製備方法)	our Company	CN202211513521.8	Invention Patent	November 29, 2042	PRC

No.	Patent	Patentee	Patent Number	Patent Type	Expiry Date	Place of Registration
16.	LDMOS device structure and manufacturing method thereof (LDMOS器件結構及其製造方法)	our Company	CN202111118014.X	Invention Patent	September 21, 2041	PRC
17.	Air gap isolation structure of trench-type MOSFET and manufacturing method thereof (一種溝槽型MOSFET的氣隙隔離結構及其製造方法)	our Company	CN202310201463.3	Invention Patent	February 27, 2043	PRC
18.	Silicon carbide MOSFET device and manufacturing method thereof (碳化矽MOSFET器件及其製造方法)	our Company	CN202110897831.3	Invention Patent	August 4, 2041	PRC
19.	VDMOS device and manufacturing method thereof (VDMOS器件及其製造方法)	our Company	CN202111224609.3	Invention Patent	October 19, 2041	PRC
20.	Method for manufacturing trench-gate MOSFET device (溝槽柵MOSFET器件的製造方法)	our Company	CN202111121658.4	Invention Patent	September 23, 2041	PRC
21.	Air gap isolation structure of trench-type MOSFET and manufacturing method thereof (一種溝槽型MOSFET的氣隙隔離結構及其製造方法)	our Company	CN202310200365.8	Invention Patent	February 27, 2043	PRC
22.	Method for manufacturing trench-type MOSFET (一種溝槽型MOSFET的製造方法)	our Company	CN202211271251.4	Invention Patent	October 17, 2042	PRC
23.	Super-junction VDMOS structure with low on-resistance (低導通電阻的超結VDMOS結構)	our Company	CN202111584948.2	Invention Patent	December 22, 2041	PRC
24.	Super-junction device with improved voltage process window (提升耐壓工藝窗口的超結器件)	our Company	CN202111487782.2	Invention Patent	December 7, 2041	PRC
25.	Layout of power semiconductor device (一種功率半導體器件版圖)	our Company	CN202411793170.X	Invention Patent	December 5, 2044	PRC
26.	Layout of power semiconductor device (一種功率半導體器件版圖)	our Company	CN202411793500.5	Invention Patent	December 5, 2044	PRC
27.	Shielded gate trench device with MGD structure and manufacturing method thereof (一種具有MGD結構的屏蔽柵溝槽器件及其製作方法)	our Company	CN202410892640.1	Invention Patent	July 2, 2044	PRC

No.	Patent	Patentee	Patent Number	Patent Type	Expiry Date	Place of Registration
28. .	Power semiconductor module (半導體功率模塊)	our Company	ZL202530258198.2	Design Patent	May 8, 2040	PRC
29. .	Method for manufacturing trench-type MOSFET (製造溝槽型MOSFET的方法)	our Company	I773605	Invention Patent	December 2, 2041	Taiwan
30. .	Method for manufacturing silicon carbide MOSFET device (碳化矽MOSFET器件的製造方法)	our Company	I785806	Invention Patent	September 15, 2041	Taiwan
31. .	LDMOS transistor and manufacturing method thereof (LDMOS電晶體及其製造方法)	our Company	I802048	Invention Patent	October 17, 2041	Taiwan
32. .	SiC MOSFET device and manufacturing method thereof (SiC MOSFET器件及其製造方法)	our Company	I812995	Invention Patent	August 10, 2041	Taiwan
33. .	LDMOS transistor and method for manufacturing the same	our Company	11757035	Invention Patent	January 13, 2039	United States
34. .	Silicon carbide MOSFET device and manufacturing method thereof	our Company	11894440	Invention Patent	September 19, 2041	United States
35. .	Ldmos transistor and manufacturing method thereof	our Company	12279442	Invention Patent	October 21, 2041	United States
36. .	Trench-type MOSFET and method for manufacturing the same	our Company	12176432	Invention Patent	June 11, 2041	United States
37. .	Shielded-gate-trench semiconductor structure and shielded-gate-trench semiconductor device	our Company	12513964	Invention Patent	September 15, 2042	United States
38. .	SWITCHING CONVERTER EQUIPPED WITH NEGATIVE CURRENT TRACKING CONTROL (네거티브 전류 트래킹 제어 기능이 구비된 스위칭 컨버터)	SMI	10-2733873	N/A	April 6, 2043	South Korea
39. .	CLOCK AND DATA RECOVERY DEVICE (클럭 데이터 복원 장치)	SMI	10-2733873	N/A	August 25, 2042	South Korea
40. .	3 LEVEL CONVERTER WITH FLYING CAPACITOR VOLTAGE BALANCING CIRCUIT (플라잉 커패시터 전압 밸런싱 회로를 포함하는 3레벨 컨버터)	SMI	10-2642713	N/A	June 6, 2042	South Korea

No.	Patent	Patentee	Patent Number	Patent Type	Expiry Date	Place of Registration
41. .	3 LEVEL BUCK-BOOST CONVERTER WITH FLYING CAPACITOR VOLTAGE BALANCING CIRCUIT 플라잉 커패시터 전압 밸런싱 회로를 포함하는 3 레벨 벅-부스트 컨버터	SMI	10-2626361	N/A	May 17, 2042	South Korea
42. .	SWITCHED-CAPACITOR CONVERTER (스위치 커패시터 컨버터)	SMI	10-2678371	N/A	December 16, 2041	South Korea
43. .	POWER CONVERSION CIRCUIT WITH BATTERY CELL BALANCING (배터리 셀 밸런싱 기능을 포함하는 전력 변환 회로)	SMI	10-2528454	N/A	January 5, 2041	South Korea
44. .	POWER SUPPLY CIRCUIT (전원 공급 회로)	SMI	10-2382987	N/A	November 11, 2040	South Korea
45. .	SWITCHED CAPACITOR CONVERTER HAVING VARIABLE VOLTAGE CONVERSION RATIO (가변 전압 변환비를 갖는 스위치드 커패시터 컨버터)	SMI	10-2439280	N/A	November 1, 2040	South Korea
46. .	COULOMB COUNTER BASED BATTERY STATE OF CHARGE ESTIMATION APPARATUS AND METHOD (쿨롱 카운터 기반의 배터리 충전상태 추정장치 및 방법)	SMI	10-2382988	N/A	May 10, 2040	South Korea
47. .	SWITCHED-CAPACITOR CONVERTER (스위치 커패시터 컨버터)	SMI	10-2355293	N/A	September 26, 2039	South Korea
48. .	A POWER MANAGEMENT APPARATUS CAPABLE OF SWITCHING A PLURALITY OF BATTERY CELLS IN SERIES OR IN PARALLEL (복수의 배터리 셀의 직렬, 병렬 전환이 가능한 전력관리장치)	SMI	10-2196926	N/A	July 9, 2039	South Korea

No.	Patent	Patentee	Patent Number	Patent Type	Expiry Date	Place of Registration
49. .	A POWER MANAGEMENT DEVICE USABLE FOR A BATTERY HAVING A PLURALITY OF CELLS CONNECTED IN SERIES (복수의 셀이 직렬 연결된 배터리에 사용 가능한 전력관리장치)	SMI	10-2236017	N/A	June 9, 2039	South Korea
50. .	CONVERTER FOR SENSING CURRENT DYNAMICALLY (동적으로 전류를 센싱하는 컨버터)	SMI	10-1979622	N/A	July 12, 2037	South Korea
51. .	Buck boost converter and control method thereof	SMI	US9,973,090B1	N/A	October 19, 2036	United States
52. .	GATE DRIVING CIRCUIT AND GATE CLOCK GENERATING CIRCUIT (게이트구동회로 및 게이트 클럭생성회로)	SMI	10-1869421	N/A	October 5, 2036	South Korea
53. .	SINGLE INDUCTOR MULTI-OUTPUT CONVERTER (싱글인덕터 멀티아웃풋 컨버터)	SMI	10-1869408	N/A	July 3, 2035	South Korea
54. .	APPARATUS AND METHOD FOR MEASURING BATTERY RESIDUAL QUANTITY (배터리잔량 측정 장치 및 방법)	SMI	10-1653967	N/A	September 22, 2034	South Korea
55. .	LED LIGHT EMITTING DEVICE AND METHOD OF DRIVING THE SAME	SMI	US8,525,433B2	N/A	June 28, 2030	United States
56. .	Level shifter and driving circuit including the same	SMI	US7,893,730B2	N/A	February 3, 2030	United States
57 . .	Super-junction device (超結器件)	our Company	12520541	Invention Patent	February 28, 2043	United States
58 . .	Split-gate power MOS device and manufacturing method thereof (分離柵功率MOS器件及其製造方法)	our Company	12581679	Invention Patent	August 14, 2042	United States
59 . .	Silicon carbide mosfet device and manufacturing method thereof (碳化矽MOSFET器件及其製造方法)	our Company	12538723	Invention Patent	August 4, 2042	United States

As of the Latest Practicable Date, we had applied for the following patents which we consider to be or may be material to our business:

No.	Patent	Patentee	Application No.	Patent Type	Application Date	Place of Registration
1. . .	Power switching device (一種功率開關器件)	our Company	CN202411269299.0	Invention Patent	September 10, 2024	PRC
2. . .	Power switching device (一種功率開關器件)	our Company	CN202411266088.1	Invention Patent	September 10, 2024	PRC
3. . .	Method for manufacturing semiconductor trench structure thereof (一種半導體溝槽結構的製造方法)	our Company	CN202311703375.X	Invention Patent	December 12, 2023	PRC
4. . .	High-speed low-power DDI driver (高速低功耗DDI驅動)	our Company	2025102790099	Invention Patent	March 10, 2025	PRC
5. . .	Semiconductor device and manufacturing method thereof (半導體器件及其製造方法)	our Company	202510510200X	Invention Patent	April 22, 2025	PRC
6. . .	Method for manufacturing trench-type MOSFET	our Company	US18/299245	Invention Patent	April 12, 2023	United States
7. . .	Super-junction device and manufacturing method thereof	our Company	US17/946100	Invention Patent	September 16, 2022	United States
8. . .	Trench Gate Semiconductor Device and Method for Manufacturing the Same	our Company	18946945	Invention Patent	November 14, 2024	United States
9. . .	Trench Gate Semiconductor Device	our Company	19033515	Invention Patent	January 22, 2025	United States
10 . .	Trench-type MOSFET device and manufacturing method thereof (溝槽MOSFET器件及其製造方法)	our Company	2025103122259	Invention Patent	March 14, 2025	PRC
11 . .	Semiconductor power device and manufacturing method thereof (一種半導體功率器件及其製造方法)	our Company	2025112847939	Invention Patent	September 9, 2025	PRC
12 . .	Semiconductor structure (一種半導體結構)	our Company	2025220135240	Utility Model Patent	September 17, 2025	PRC
13 . .	Semiconductor structure (一種半導體結構)	our Company	2026200793904	Utility Model Patent	January 21, 2026	PRC
14 . .	Semiconductor device and manufacturing method thereof (一種半導體器件及其製備方法)	our Company	2026106121290	Invention Patent	May 6, 2026	PRC
15 . .	Trench-type MOSFET device and manufacturing method thereof (溝槽MOSFET器件及其製造方法)	our Company	US19/565,586	Invention Patent	March 13, 2026	United States
16 . .	Semiconductor structure (一種半導體結構)	our Company	US19/642,661	Invention Patent	April 9, 2026	United States

(c) Integrated Circuit Layout Designs

As of the Latest Practicable Date, we had registered the following integrated circuit layout designs that we consider to be or may be material to our business:

No.	Name of circuit design	Registered Owner	Registration No.	Application Date	Place of Registration
1.	Enhancement Planar MOS_X43	our Company	BS.215598482	August 12, 2021	PRC
2.	Enhancement Planar MOS_W14	our Company	BS.215598520	August 12, 2021	PRC
3.	Enhancement Planar MOS_X45	our Company	BS.215598962	August 13, 2021	PRC
4.	Enhancement Planar MOS_X51	our Company	BS.215598989	August 13, 2021	PRC
5.	Enhancement Planar MOS_W18	our Company	BS.215598709	August 13, 2021	PRC
6.	Enhancement Planar MOS_W19	our Company	BS.215598938	August 13, 2021	PRC
7.	Enhancement Planar MOS_W12	our Company	BS.215598954	August 13, 2021	PRC
8.	Enhancement Planar MOS_W16	our Company	BS.215598539	August 12, 2021	PRC
9.	Enhancement SGTMOS_M15G08A	our Company	BS.235524182	April 13, 2023	PRC
10.	Enhancement SGTMOS_MG36A	our Company	BS.235524220	April 13, 2023	PRC
11.	Enhancement SGTMOS_F06A65AN	our Company	BS.235524352	April 13, 2023	PRC
12.	Enhancement SGTMOS_MA04A61AN	our Company	BS.235524212	April 14, 2023	PRC
13.	SM5810	our Company	BS.235553603	July 7, 2023	PRC
14.	SM5820	our Company	BS.23555362X	July 7,2023	PRC
15.	SM5840	our Company	BS.235553638	July 7, 2023	PRC
16.	SM4821	our Company	BS.235558907	July 25, 2023	PRC
17.	SM5603	our Company	BS.235553530	July 7, 2023	PRC
18.	SM4813	our Company	BS.235553387	July 7, 2023	PRC
19.	SM4812	our Company	BS.235553352	July 7, 2023	PRC
20.	SM8101	our Company	BS.235554391	July 11, 2023	PRC
21.	SM4808	our Company	BS.235553123	July 6, 2023	PRC
22.	SM4809	our Company	BS.23555331X	July 7, 2023	PRC
23.	Enhancement SJMOS_LG06	our Company	BS.235566160	August 15, 2023	PRC
24.	Enhancement SJMOS_SJ03A	our Company	BS.235566179	August 15, 2023	PRC
25.	Enhancement SiCMOS_XAA2C03AB	our Company	BS.235566195	August 15, 2023	PRC
26.	SiC_MPS_ECPZA01_1200V	our Company	BS.235566187	August 15, 2023	PRC
27.	SiC_MPS_ECPZA01_650V	our Company	BS.235566152	August 15, 2023	PRC
28.	SM4820	our Company	BS.235558893	July 25, 2023	PRC
29.	1200V_SiC_Mosfet (XAA2A09AB)	our Company	BS.245566759	August 29, 2024	PRC
30.	30V_SGT (F03A89AN)	our Company	BS.24556666X	August 29, 2024	PRC
31.	60V_SGT (F06A94AN)	our Company	BS.245566708	August 29, 2024	PRC
32.	100V_SGT (F10A78AN)	our Company	BS.245566716	August 29, 2024	PRC
33.	40V_SGT (F04A88AN)	our Company	BS.245566678	August 29, 2024	PRC
34.	SM5328BF	our Company	BS.245567348	September 2, 2024	PRC

No.	Name of circuit design	Registered Owner	Registration No.	Application Date	Place of Registration
35. .	SM4852_BB	our Company	BS.245567291	September 2, 2024	PRC
36. .	SM4852_CTL	our Company	BS.245567313	September 2, 2024	PRC
37. .	SM5112	our Company	BS.24556733X	September 2, 2024	PRC
38. .	SM5109CF	our Company	BS.245567321	September 2, 2024	PRC
39 . .	Enhancement SGT MOS_FDE2A8CBN	our Company	BS.255583761	October 21, 2025	PRC
40 . .	Enhancement SGT MOS_F03A3ACN	our Company	BS.255583788	October 21, 2025	PRC
41 . .	Enhancement SGT MOS_FAD04B6BAN	our Company	BS.255583796	October 21, 2025	PRC
42 . .	Enhancement SGT MOS_F08A74AN	our Company	BS.255583826	October 21, 2025	PRC
43 . .	Enhancement SGT MOS_FD10A8DAN	our Company	BS.255583842	October 21, 2025	PRC
44 . .	Enhancement SJ MOS_FJ65A4DAN	our Company	BS.255583850	October 21, 2025	PRC
45 . .	Enhancement SiC MOS_X65ZA30	our Company	BS.255583893	October 21, 2025	PRC
46 . .	Enhancement SiC MOS_XA2A16AB	our Company	BS.255583915	October 21, 2025	PRC
47 . .	Enhancement SiC MOS_GCA2A18AN	our Company	BS.255583923	October 21, 2025	PRC
48 . .	Enhancement SiC MOS_XA7ZA31	our Company	BS.255583931	October 21, 2025	PRC
49 . .	SM4831	our Company	BS.255584776	October 23, 2025	PRC
50 . .	SM5452A	our Company	BS.255584784	October 23, 2025	PRC

(d) Domain Names

As of the Latest Practicable Date, we had registered the following domain names, which we consider to be or may be material to our Group's business:

No.	Domain name	Registered owner	Registration date	Expiry date
1. . .	silicon-magic.com	our Company	August 17, 2020	August 17, 2026
2. . .	silicon-top.com	Hangzhou Xintong	August 8, 2023	August 8, 2026
3. . .	siliconmitus.com	SMI	February 14, 2007	February 14, 2030

Save as disclosed above, as of the Latest Practicable Date, there were no other trade or service marks, patents, intellectual or industrial property rights which were material in relation to our business.

C. FURTHER INFORMATION ABOUT OUR DIRECTORS AND SUBSTANTIAL SHAREHOLDERS

1. Directors and Chief Executive

(i) Disclosure of Interests of Our Directors and Chief Executive

Immediately following completion of the [**REDACTED**] (assuming that the [**REDACTED**] is not exercised and no other changes are made to the issued share capital of our Company between the Latest Practicable Date and [**REDACTED**]), the interests and short positions of each of our Directors and chief executive in Shares, underlying Shares and debentures of our Company or any associated corporation (within the meaning of Part XV of the SFO) which will have to be notified to us and the Stock Exchange pursuant to Divisions 7 and 8 of Part XV of the SFO (including interests and short positions which he has taken or deemed to have under such provisions of the SFO) or which will be required, pursuant to section 352 of the SFO, to be entered in the register referred to therein, or will be required, pursuant to the Model Code for Securities Transactions by Directors of Listed Issuers as set out in Appendix C3 of the Listing Rules to be notified to us and the Stock Exchange will be as follows:

Interest in our Company

Name	Position	Nature of interest	Number and class of Shares to be held after the [REDACTED]	Approximate percentage of shareholding interests in the Unlisted Shares/ H Shares (where appropriate) immediately following completion of the [REDACTED][(4)]
Dr. Ren	Chairperson of our Board, executive Director and chief executive officer	Interest in controlled corporation[(2)]	[REDACTED] (Unlisted Shares) (L)	[REDACTED]%
			[REDACTED] (H Shares)	[REDACTED]%
		Interest held jointly with another person[(3)]	[REDACTED] (Unlisted Shares) (L)	[REDACTED]%
			[REDACTED] (H Shares) (L)	[REDACTED]%
Dr. Huh	Vice chairperson of our Board and executive Director	Beneficial owner	[REDACTED] (Unlisted Shares) (L)	[REDACTED]%
			[REDACTED] (H Shares) (L)	[REDACTED]%
		Interest in controlled corporation[(4)]	[REDACTED] (Unlisted Shares) (L)	[REDACTED]%
			[REDACTED] (H Shares) (L)	[REDACTED]%
Mr. Xie Li	Non-executive Director	Interest in controlled corporation[(5)]	[REDACTED] (H Shares) (L)	[REDACTED]%

Notes:

(1) The letter "L" denotes the person's long position in our Shares.

(2) As of the Latest Practicable Date, Hangzhou Qinxin was the general partner of Hangzhou Moxin and Hangzhou Qinxin was in turn held as to 80% by Dr. Ren. Accordingly, each of Hangzhou Qinxin and Dr. Ren was deemed to be interested in the Shares directly held by Hangzhou Moxin for the purpose of the SFO.

(3) Pursuant to an acting-in-concert agreement dated June 19, 2025, Hangzhou Moxin, Smart Advantage, Smart Wealth, Hangzhou Qinxin, Bright Shine, Dr. Ren, and Dr. Su are parties acting in concert regarding decisions at the general meetings of our Company which will continue after the [**REDACTED**]. As such, under the SFO, each of them is deemed to be interested in the Shares in which the others are interested in.

(4) As of the Latest Practicable Date, Dr. Huh owned as to 99.99997% interests of Smart Advantage as the sole limited partner. Accordingly, Dr. Huh was deemed to be interested in the Shares directly held by Smart Advantage for the purpose of the SFO.

(5) As of the Latest Practicable Date, Zhejiang Haibang Private Equity Management Co., Ltd.* (浙江海邦私募基金管理有限公司)) ("**Haibang Management**") was the general partner of each of Hangzhou Haibang Qiyue Equity Investment Partnership (L.P.)* (杭州海邦啟悦股權投資合夥企業(有限合夥)) ("**Haibang Qiyue**"), Hangzhou Haibang Ruibo Equity Investment Partnership (L.P.)* (杭州海邦睿柏股權投資合夥企業(有限合夥)) ("**Haibang Ruibo"**) and Longyou Haibang Xinzhi Venture Investment Partnership (L.P.)* (龍游海邦新智創業投資合夥企業（有限合夥）) ("**Longyou Haibang Xinzhi**"). In addition, Ningbo Haibang Xingcai Venture Investment Partnership (L.P.)* (寧波海邦星材創業投資合夥企業(有限合夥)) ("**Ningbo Haibang**")'s general partner was Hangzhou Haibang Fenghua Investment Management Co., Ltd.* (杭州海邦灃華投資管理有限公司), which was in turn wholly owned by Haibang Management. Haibang Management was owned as to 50% by Mr. Xie Li. Therefore, Mr. Xie Li was deemed to be interested in the Shares held by Haibang Qiyue, Haibang Ruibo, Longyou Haibang Xinzhi and Ningbo Haibang for the purpose of the SFO.

As of the Latest Practicable Date, none of the Directors or their respective spouses and children under 18 years of age had been granted by our Company or had exercised any rights to subscribe for shares or debentures of our Company or any of its associated corporations.

(ii) Particulars of service agreements and appointment letters

Our Company [has entered] into a service agreement or an appointment letter with each of our Directors which contains provisions in relation to, among other things, compliance of relevant laws and regulations and observation of the Articles of Association.

The principal particulars of these service agreements and appointment letters are (a) each of the service agreements or the appointment letters is for a term of three years following the date of his/her appointment; and (b) each of the service agreements or the appointment letters is subject to termination in accordance with their respective terms. The service agreements and appointment letters may be renewed in accordance with our Articles of Association and the applicable rules.

Save as disclosed above, none of the Directors has or is proposed to enter into a service contract with any member of our Group (other than contracts expiring or determinable by the relevant employer within one year without the payment of compensation other than statutory compensation).

(iii) Directors' remuneration

For remuneration details of all Directors during the Track Record Period, please refer to Note 44 to the Accountant's Report as set out in Appendix I to this document.

During the Track Record Period, no remuneration was paid by us nor receivable by Directors or the five highest remunerated individuals as incentives for joining or as rewards upon joining our Company. During the Track Record Period, no remuneration was paid by us nor receivable by Directors, past Directors, or the five highest remunerated individuals as compensation for leaving positions relating to management affairs in any subsidiary of our Company.

During the Track Record Period, none of our Directors have waived any remuneration. Save as disclosed above, during the Track Record Period, no other amounts shall be paid or payable by us or any of our subsidiaries to the Directors or the five highest remunerated individuals.

2. Substantial Shareholders

Interest in the Share of our Company

Save as disclosed in the section headed "Substantial Shareholders" in this document, our Directors are not aware of any other person who will, immediately following the completion of the [**REDACTED**], have an interest or a short position in our Shares or underlying Shares of our Company which would be required to be disclosed to our Company and the Stock Exchange under the provisions of Divisions 2 and 3 of Part XV of the SFO or will, directly or indirectly, be interested in 10% or more of the nominal value of any class of share capital carrying rights to vote in all circumstances at general meetings of our Company.

3. Disclaimers

Save as disclosed in this document:

(i) none of the Directors or chief executive of our Company has any interests and short positions in our Shares, underlying Shares and debentures of our Company or any associated corporation (within the meaning of Part XV of the SFO) which will have to be notified to us and the Stock Exchange pursuant to Divisions 7 and 8 of Part XV of the SFO (including interests and short positions which he has taken or is deemed to have under provisions of SFO) or which will be required, pursuant to section 352 of the SFO, to be entered in the register referred to therein, or will be required, pursuant to the Model Code for Securities Transactions by Directors of Listed Issuers to be notified to us and the Stock Exchange, in each case once the H Shares of our Company are [**REDACTED**];

(ii) so far is known to any Director or chief executive of our Company, no other person (other than a Director or chief executive of our Company) will, immediately following completion of the [**REDACTED**], have interests or short positions in our Shares and underlying Shares which would fall to be disclosed to our Company and the Stock Exchange under the provisions of Divisions 2 and 3 of Part XV of the SFO or (not being a member of our Group), be interested, directly or indirectly, in 10% or more of the nominal value of any class of share capital carrying rights to vote in all circumstances at general meetings of any member of our Group;

(iii) save as disclosed in the "[**REDACTED**]" section in this document, no commissions, discounts, brokerages or other special terms have been granted in connection with the issue or sale of any Shares in or debentures of our Company within the two years ended on the date of this document;

(iv) none of the parties listed in the paragraph headed "Qualification of Experts" of this Appendix (i) is interested legally or beneficially in any of the Shares of our Company or any shares in any of its subsidiaries; or (ii) has any right (whether legally enforceable or not) to subscribe for or to nominate persons to subscribe for the securities of our Company;

(v) none of our Directors nor any of the experts listed in the paragraph headed "Qualification of Experts" of this Appendix is materially interested in any contract or arrangement subsisting at the date of this document which is significant in relation to the business of our Group taken as a whole;

(vi) none of our Directors, their close associates or any Shareholder of our Company (which to the best of our Directors' knowledge, information and belief owns more than 5% of our Company's issued share capital) has any interest in our Group's five largest suppliers or five largest customers for each year/period during the Track Record Period; and

(vii) none of our Directors is a director or employee of a company that has an interest in the share capital of our Company which, once the H Shares are [**REDACTED**] on the Hong Kong Stock Exchange, would have to be disclosed pursuant to Divisions 2 and 3 of Part XV of the SFO.

D. [REDACTED] ESOP

The following is a summary of the principal terms of the [**REDACTED**] ESOP. The terms of the [**REDACTED**] ESOP are not subject to the provisions of Chapter 17 of the Listing Rules as it does not involve the grant of share options or awards by our Company after [**REDACTED**]. Given the underlying Shares attaching to the partnership interests in the ESOP Platforms (the "**Virtual Shares**") under the [**REDACTED**] ESOP have already been issued to the ESOP Platforms as of the Latest Practicable Date, there will not be any dilutive effect to the issued Shares as a result of the operation of the [**REDACTED**] ESOP.

(a) Purpose

The purpose of the [**REDACTED**] ESOP is to incentivize directors, senior management and employees of our Group to provide better services to our Group. The goal is to align employee efforts with our Company's growth and eventual to accomplish a successful [**REDACTED**] of our Shares.

(b) Eligible Participants

Eligible participants of the [**REDACTED**] ESOP shall be the employees of our Group.

(c) Administration

The [**REDACTED**] ESOP shall be administered by our Board which may delegate administration function to the general manager of our Company.

(d) Grant of Options

Pursuant to the [**REDACTED**] ESOP, our Board may grant options to an employee (the "**Grantee**") to purchase Virtual Shares (the "**Grant**").

(e) Terms of the Grant

The Grantee is required to accept the Grant by entering into an equity incentive agreement (the "**Incentive Agreement**") with, among others, the Company and the relevant ESOP Platform and its general partner, which set forth the terms and conditions of the Grant as summarized below:

– Term — the Grantee shall be entitled to immediately exercise the option at any time and for any number of times from the date of Grant to the date on which the Company is converted into joint stock company, subject to any early termination provided in the Incentive Agreement (the "**Term**").

– Exercise price — the exercise price (the "**Exercise Price**") of the option for each Virtual Share shall be determined by our Board at its sole discretion and set out in the Incentive Agreement.

- Exercise procedures — the Grantee may exercise the option granted to him within the Term by delivery to our Company a designated exercise application form accompanied by such amount representing the total Exercise Price payable by him corresponding to the number of Virtual Shares for which the option is exercised. Upon acceptance by our Company, the ESOP Platform and its general partner, the Grantee will be required to execute the partnership agreement of the relevant ESOP Platform and become a limited partner of the relevant ESOP Platform.

- Transfer of Virtual Shares — the transfer of the Virtual Shares by a Grantee shall be subject to the consent of the general partner of the relevant ESOP Platform and the restrictions set out in the Incentive Agreement. Where the general partner of the relevant ESOP Platform consents to the proposed transfer of the Virtual Shares held by a Grantee, the Grantee shall transfer all the Virtual Shares owned by him and withdraw from the ESOP Platform, unless otherwise provided in the Incentive Agreement or approved by the general partner of the relevant ESOP Platform in writing.

- Redemption by the ESOP Platform — upon the occurrence of any triggering event (including, but not limited to, (i) material breach of the Incentive Agreement by the Grantee; (ii) material breach of his duties under any agreement with our Group by the Grantee, (iii) material breach of laws and regulations applicable to our Group and/or the Grantee, (iv) termination of employment relationship with our Group, or (v) death of the Grantee) as set out in the Incentive Agreement, the general partner of the relevant ESOP Platform may redeem or otherwise require the Grantee to transfer all his Virtual Shares in such manner as the general partner may direct at the price predetermined in the Incentive Agreement.

- Realization of interests — subject to the vesting conditions and the lockup arrangements as may be determined by our Board and set out in the Incentive Agreement, the Grantee shall have the right to require the relevant ESOP Platform to redeem his vested portion of Virtual Shares at market price.

- Rights of the Grantee — the Grantee shall only entitle to the economic interests of such number of the underlying Shares held by the relevant ESOP Platform corresponding to the Virtual Shares owned by him, but not for other rights, including, but not limited to, the voting rights attached to the underlying Shares.

(h) Number of underlying Shares

The ESOP Platforms currently holds 6,646,974 Shares for [**REDACTED**] ESOP which will be [**REDACTED**] in to [**REDACTED**] Shares upon the completion of [**REDACTED**], representing approximately [**REDACTED**]% of the issued share capital of the Company immediately after the completion of the [**REDACTED**] (without taking into account Shares may be issued pursuant to the exercise of the [**REDACTED**]).

(i) Effect of alterations to share capital

In the event that the share capital of our Company alters for any reason, the number of Virtual Shares granted to the Grantee will remain unchanged but the number of underlying Shares indirectly interested by the Grantee through the ESOP Platforms will be adjusted proportionally.

(j) Further information

As of the Latest Practicable Date, all the underlying Shares, being 6,646,974 Shares, which are held by the ESOP Platforms for the purpose of [**REDACTED**] ESOP have been allocated to corresponding Virtual Shares.

The table below shows the details of underlying Shares (as allocated to the Virtual Shares) granted to our Directors and members of our senior management under the [**REDACTED**] ESOP:

Name of grantee	Position in our Group	No. of Virtual Shares	No. of underlying Shares (as adjusted for [REDACTED])	Percentage of the issued share capital of our Company after completion of the [REDACTED][(1)]
Dr. Ren	Chairperson of our Board, executive Director and chief executive officer	8,111,855	[REDACTED]	[REDACTED]%
Dr. Huh	Vice chairperson of our Board, executive Director and chief executive officer of SMI	5,000,000	[REDACTED]	[REDACTED]%
Sun Junping (孫君萍)	Supervisor	12,500	[REDACTED]	[REDACTED]%
Dr. Su	Executive vice president of administration and joint company secretary	853,641	[REDACTED]	[REDACTED]%
Liang Jianxiong (梁建雄)	Vice president of sales	800,000	[REDACTED]	[REDACTED]%
Li Xiaolei (李曉蕾)	Chief financial officer	150,000	[REDACTED]	[REDACTED]%
Kim Jong Hwan	Senior vice president of engineering of SMI	342,587	[REDACTED]	[REDACTED]%
Remaining 360 Grantees	–	13,078,777	[REDACTED]	[REDACTED]%
Other Virtual Shares to be granted[(2)]	–	450,640	[REDACTED]	[REDACTED]%

Note:

(1) Without taking into account any Shares which may be issued upon the exercise of the [**REDACTED**].

(2) These Virtual Shares will be granted prior to the [**REDACTED**].

Given that all the Virtual Shares have been granted and all the underlying Shares have been allocated to the Grantees at the time of [**REDACTED**], no further Grant will be made under the [**REDACTED**] ESOP after the [**REDACTED**].

E. OTHER INFORMATION

1. Estate Duty

Our Directors have been advised that no material liability for estate duty is likely to fall on our Company or any of our subsidiaries under the PRC laws.

2. Litigation

As of the Latest Practicable Date, we are not aware of any litigation, arbitration or claims of material importance pending or threatened against any member of our Group that could have a material adverse effect on our financial condition or results of operations.

3. Sole Sponsor

The Sole Sponsor satisfies the independence criteria applicable to sponsor set out in Rule 3A.07 of the Listing Rules.

The Sole Sponsor will be paid by our Company a fee of US$500,000 to act as the Sole Sponsor to our Company in connection with the [**REDACTED**].

4. Compliance Adviser

Our Company has appointed Quam Capital Limited as its compliance adviser in compliance with Rule 3A.19 of the Listing Rules.

5. Preliminary Expenses

We have not incurred any material preliminary expenses in relation to the incorporation of our Company.

6. Taxation of holder of H Shares

The sale, purchase and transfer of H Shares are subject to Hong Kong stamp duty if such sale, purchase and transfer are affected on the H Share register of members of our Company, including in circumstances where such transactions are affected on the Stock Exchange. The current rate of Hong Kong stamp duty for such sale, purchase and transfer is 0.1% of the consideration or, if higher, the fair value of the H Shares being sold or transferred.

7. Qualification of Experts

The following are the qualifications of the experts (as defined under the Listing Rules and the Companies (Winding Up and Miscellaneous Provisions) Ordinance) who have given opinions or advice which are contained in this document:

Name	Qualification
Huatai Financial Holdings (Hong Kong) Limited	A licensed corporation to conduct Type 1 (dealing in securities), Type 2 (dealing in futures contracts), Type 3 (leveraged foreign exchange trading), Type 4 (advising on securities), Type 6 (advising on corporate finance), Type 7 (providing automated trading services) and Type 9 (asset management) regulated activities as defined under the SFO
Jia Yuan Law Offices	Legal advisers as to PRC law
Bae, Kim & Lee LLC	Legal advisers as to South Korean law
Stephen Peepels, Esq.	Legal adviser as to export control and sanctions laws
PricewaterhouseCoopers	Certified Public Accountants under Professional Accountants Ordinance (Chapter 50 of the Laws of Hong Kong) and Registered Public Interest Entity Auditor under Accounting and Financial Reporting Council Ordinance (Chapter 588 of the Laws of Hong Kong)
Frost & Sullivan	Independent industry consultant

Name	Qualification
Lixin Certified Tax Agents (Zhejiang) Co., Ltd.	Transfer pricing consultant in PRC
PricewaterhouseCoopers Consultants (Shenzhen) Limited Hangzhou Branch	Transfer pricing consultant in PRC
Yulchon LLC	Transfer pricing consultant in South Korea

8. Consent of Experts

Each of the experts whose names is set out in paragraph 7 above [has given and has not] withdrawn its written consent to the issue of this document with the inclusion of its report and/or letter and/or legal opinion (as the case may be) and references to its name included herein in the form and context in which they respectively appear.

As of the Latest Practicable Date, none of the experts named above had any shareholding interest in our Company or any of our subsidiaries or the right (whether legally enforceable or not) to subscribe for or to nominate persons to subscribe for securities in any member of our Group.

9. Promoters

The promoters of our Company are:

(1) Vasona Technology Hong Kong Limited (瓦森納科技香港有限公司);

(2) Hangzhou Xidaxin Corporate Management Partnership (L.P.)* (杭州喜達芯企業管理合夥企業(有限合夥));

(3) Hangzhou Xihangxin Corporate Management Partnership (L.P.)* (杭州喜杭芯企業管理合夥企業(有限合夥));

(4) Hangzhou Moxin;

(5) Smart Wealth;

(6) Smart Advantage;

(7) Hangzhou Haibang Qiyue Equity Investment Partnership (L.P.)* (杭州海邦啟悅股權投資合夥企業(有限合夥));

(8) Smart Brilliant International Investment Limited (智晶國際投資有限公司);

(9) Zhuhai Weiheng Equity Investment Partnership (L.P.)* (珠海巍恒股權投資合夥企業(有限合夥), currently known as Zhuhai Weiheng Investment Partnership (L.P.)* (珠海巍恒投資合夥企業(有限合夥));

(10) HSG Growth VI Holdco B (HK) Limited;

(11) Beijing Junlian Shengyuan Equity Investment Partnership (L.P.)* (北京君聯晟源股權投資合夥企業(有限合夥));

(12) Zhuhai Junlian Xingze Equity Investment Enterprise (L.P.)* (珠海君聯星澤股權投資企業(有限合夥));

(13) Hai Feng Investment Holding Limited (海風投資有限公司);

(14) Hangzhou Xinshengwei Equity Investment Partnership (L.P.)* (杭州芯盛微股權投資合夥企業(有限合夥));

(15) Hefei Huaxin Kerui IC Investment Partnership (L.P.)* (合肥華芯科瑞集成電路投資合夥企業(有限合夥));

(16) Hefei Huadeng Erqi IC Industry Investment Partnership (L.P.)* (合肥華登二期集成電路產業投資合夥企業(有限合夥));

(17) Cosmic Warrior (HK) Limited;

(18) Hubei Xiaomi Changjiang Industry Fund Partnership (L.P.)* (湖北小米長江產業基金合夥企業(有限合夥));

(19) Contemporary Amperex Technology Co., Limited (寧德時代新能源科技股份有限公司);

(20) Dr. Huh;

(21) National IC Industry Investment Fund Phase II Co., Ltd.* (國家集成電路產業投資基金二期股份有限公司);

(22) Hangzhou Xinchengwei Equity Investment Partnership (L.P.)* (杭州芯成微股權投資合夥企業(有限合夥));

(23) Hangzhou Xinyuwei Equity Investment Partnership (L.P.)* (杭州芯宇微股權投資合夥企業(有限合夥));

(24) Guangzhou Guangqi Xinmai Management Consultancy Partnership (L.P.)* (廣州廣祺欣邁管理諮詢合夥企業(有限合夥);

(25) Zhuhai Hongtu Zhanlu Equity Investment Partnership (L.P.)* (珠海市紅土湛盧股權投資合夥企業(有限合夥));

(26) Jiaxing Hengjunbang Equity Investment Partnership (L.P.)* (嘉興恒雋邦股權投資合夥企業(有限合夥));

(27) Hangzhou Fuyang Xiangheng Equity Investment Partnership (L.P.)* (杭州富陽項恒股權投資合夥企業(有限合夥));

(28) Suzhou Huaye Zhiyuan No. 3 Equity Investment Partnership (L.P.)* (蘇州華業致遠三號股權投資合夥企業(有限合夥));

(29) Jiaxing Taixin Keqi Venture Investment Partnership (L.P.)* (嘉興泰芯科啟創業投資合夥企業(有限合夥));

(30) Hangzhou Xingcheng Lianxin Venture Investment Partnership (L.P.)* (杭州星成聯芯創業投資合夥企業(有限合夥));

(31) Hangzhou Yuxin Venture Investment Partnership (L.P.)* (杭州寓鑫創業投資合夥企業(有限合夥));

(32) Yibin Lvneng Equity Investment Partnership (L.P.)* (宜賓綠能股權投資合夥企業(有限合夥));

(33) Guangdong Changtuoshi Venture Investment Partnership (L.P.)* (廣東長拓石創業投資合夥企業(有限合夥));

(34) Hangzhou Xinlanwei Venture Investment Partnership (L.P.)* (杭州芯嵐微創業投資合夥企業(有限合夥));

(35) Zhuhai Junlian Xingchi Venture Investment Enterprise (L.P.)* (珠海君聯星馳創業投資企業(有限合夥));

(36) Hangzhou Huaxin Yunmai Equity Investment Partnership (L.P.)* (杭州華芯雲邁股權投資合夥企業(有限合夥));

(37) Yibin Chendao New Energy Industry Equity Investment Partnership (L.P.)* (宜賓晨道新能源產業股權投資合夥企業(有限合夥));

(38) Zhejiang Jinkong Investment Co., Ltd.* (浙江金控投資有限公司) (currently known as Zhejiang Province Innovation Capital Investment Co., Ltd.* (浙江省創新資本投資有限公司);

(39) Hangzhou Haibang Ruibo Equity Investment Partnership (L.P.)* (杭州海邦睿柏股權投資合夥企業(有限合夥));

(40) Ningbo Haibang Xingcai Venture Investment Partnership (L.P.)* (寧波海邦星材創業投資合夥企業(有限合夥)); and

(41) Qingdao Jingque Xinyang Technology Center (L.P.)* (青島精確芯陽科技中心(有限合夥)).

Within the two years immediately preceding the date of this document, no cash, securities or other benefit have been paid, allotted or given or have been proposed to be paid, allotted or given to the above promoters in connection with the [**REDACTED**] or related transactions described in this document.

10. Bilingual Document

The English language and Chinese language versions of this document are being published separately.

11. Binding Effect

This document shall have the effect, if an application is made in pursuance of this document, of rendering all persons concerned bound by all of the provisions (other than the penal provisions) of Sections 44A and 44B of the Companies (Winding Up and Miscellaneous Provisions) Ordinance in so far as applicable.

12. No Material Adverse Change

Our Directors confirm that there has been no material adverse change in the business operation and financial position or prospects of our Group since April 30, 2026 (being the date to which the latest audited consolidated financial statements of our Group were prepared).

13. Miscellaneous

(a) Save as disclosed in this document, within the two years immediately preceding the date of this document:

(i) no share or loan capital or debenture of our Company or any of our subsidiaries has been issued or agreed to be issued or is proposed to be issued for cash or as fully or partly paid other than in cash or otherwise; and

(ii) no commissions, discounts, brokerages or other special terms have been granted or agreed to be granted in connection with the issue or sale of any share or loan capital of our Company or any of our subsidiaries.

(b) Save as disclosed in this document:

(i) there are no founder, management or deferred shares nor any debentures in our Company or any of our subsidiaries;

(ii) there is no arrangement under which future dividends are waived or agreed to be waived;

(iii) there are no contracts for hire or hire purchase of plan to or by us for a period of over one year which are substantial in relation to our business;

(iv) no share or loan capital or debenture of our Company or any of our subsidiaries is under option or is agreed conditionally or unconditionally to be put under option;

(v) no commissions, discounts, brokerages or other special terms have been granted in connection with the issue or sale of any share or loan capital of our Company or any of its subsidiaries by our Company for subscribing or agreeing to subscribe, or procuring or agreeing to procure subscriptions, for any shares in or debentures of our Company or any of our subsidiaries;

(vi) save for our H Shares to be [**REDACTED**] in connection with the [**REDACTED**], none of our equity and debt securities are [**REDACTED**] or [**REDACTED**] with in any other stock exchange nor is any [**REDACTED**] or permission to [**REDACTED**] being or proposed to be sought; and

(vii) there are no outstanding debentures or convertible debt securities of our Company or any of our subsidiaries.

(c) Save as disclosed in this document, none of our Directors or experts (as named in this document) have any interest, direct or indirect, in any assets which have been, within the two years immediately preceding the date of this document, acquired or disposed of by or leased to, any member of our Group, or are proposed to be acquired or disposed of by or leased to any member of our Group.

(d) There has not been any interruption in the business of our Group which may have or has had a significant effect on the financial position of our Group in the 12 months preceding the date of this document.